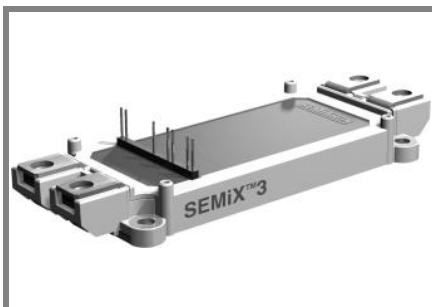


# SEMIX 353GB126HD



**SEMIX<sup>®</sup> 3**

## Trench IGBT Modules

### SEMIX 353GB126HD

[www.DataSheet4U.com](http://www.DataSheet4U.com)

Preliminary Data

### Features

- Homogeneous Si
- Trench = Trenchgate technology
- $V_{CE(sat)}$  with positive temperature coefficient
- High short circuit capability

### Typical Applications

- AC inverter drives
- UPS
- Electronic Welding

### Remarks

- Case temperatur limited to  $T_C=125^{\circ}\text{C}$  max.
- Not for new design

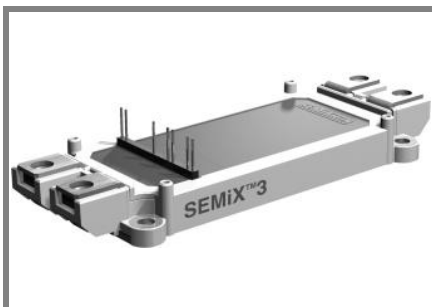


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Absolute Maximum Ratings		$T_{case} = 25^{\circ}\text{C}$ , unless otherwise specified		
Symbol	Conditions	Values	Units	
<b>IGBT</b>				
$V_{CES}$	$T_j = 25^{\circ}\text{C}$	1200	V	
$I_C$	$T_j = 150^{\circ}\text{C}$	$T_c = 25^{\circ}\text{C}$	365	A
		$T_c = 80^{\circ}\text{C}$	255	A
$I_{CRM}$	$I_{CRM}=2 \times I_{Cnom}$	450	A	
$V_{GES}$		$\pm 20$	V	
$t_{psc}$	$V_{CC} = 600\text{ V}; V_{GE} \leq 20\text{ V}; T_j = 125^{\circ}\text{C}$ $V_{CES} < 1200\text{ V}$	10	$\mu\text{s}$	
<b>Inverse Diode</b>				
$I_F$	$T_j = 150^{\circ}\text{C}$	$T_c = 25^{\circ}\text{C}$	330	A
		$T_c = 80^{\circ}\text{C}$	225	A
$I_{FRM}$	$I_{FRM}=2 \times I_{Fnom}$	450	A	
$I_{FSM}$	$t_p = 10\text{ ms}; \text{sin.}$	$T_j = 25^{\circ}\text{C}$	1700	A
<b>Module</b>				
$I_t(RMS)$		600	A	
$T_{vj}$		- 40 ... + 150	$^{\circ}\text{C}$	
$T_{stg}$		- 40 ... + 125	$^{\circ}\text{C}$	
$V_{isol}$	AC, 1 min.	4000	V	

Characteristics		$T_{case} = 25^{\circ}\text{C}$ , unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
<b>IGBT</b>					
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 9\text{ mA}$	5	5,8	6,5	V
$I_{CES}$	$V_{GE} = 0\text{ V}, V_{CE} = V_{CES}$			0,3	mA
$V_{CE0}$		$T_j = 25^{\circ}\text{C}$	1	1,2	V
		$T_j = 125^{\circ}\text{C}$	0,9	1,1	V
$r_{CE}$	$V_{GE} = 15\text{ V}$	$T_j = 25^{\circ}\text{C}$	3,1	4,2	$\text{m}\Omega$
		$T_j = 125^{\circ}\text{C}$	4,9	6	$\text{m}\Omega$
$V_{CE(sat)}$	$I_{Cnom} = 225\text{ A}, V_{GE} = 15\text{ V}$	$T_j = 25^{\circ}\text{C}_{chiplev.}$	1,7	2,1	V
		$T_j = 125^{\circ}\text{C}_{chiplev.}$	2	2,4	V
$C_{res}$	$V_{CE} = 25, V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$	16		nF
$C_{oes}$			0,84		nF
$C_{res}$			0,73		nF
$Q_G$	$V_{GE} = -8 \dots +15\text{V}$		1800		nC
$t_{d(on)}$	$R_{Gon} = 2\ \Omega$	$V_{CC} = 600\text{V}$ $I_{Cnom} = 225\text{A}$	265		ns
$t_r$			55		ns
$E_{on}$	$R_{Goff} = 2\ \Omega$	$T_j = 125^{\circ}\text{C}$	26,5		mJ
$t_{d(off)}$			585		ns
$t_f$			120		ns
$E_{off}$			32,5		mJ
$R_{th(j-c)}$	per IGBT			0,1	K/W

# SEMiX 353GB126HD



**SEMiX<sup>®</sup> 3**

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#### Preliminary Data

#### Features

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#### Typical Applications

- AC inverter drives
- UPS
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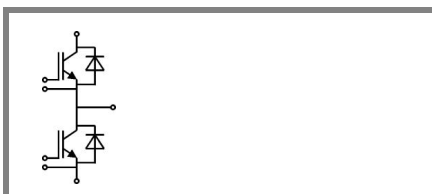
#### Remarks

- Case temperatur limited to  $T_C=125^{\circ}\text{C}$  max.
- Not for new design

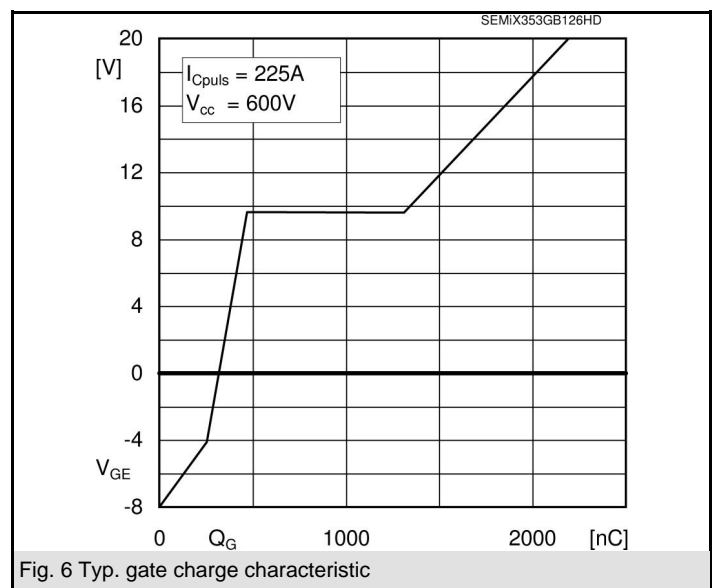
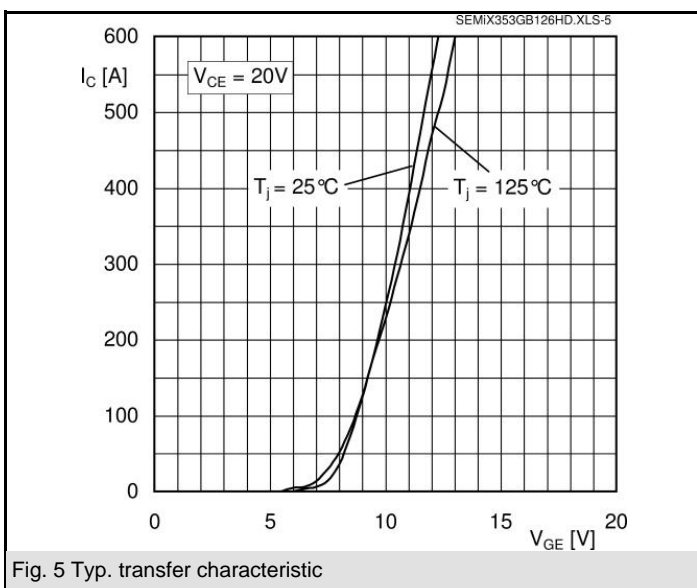
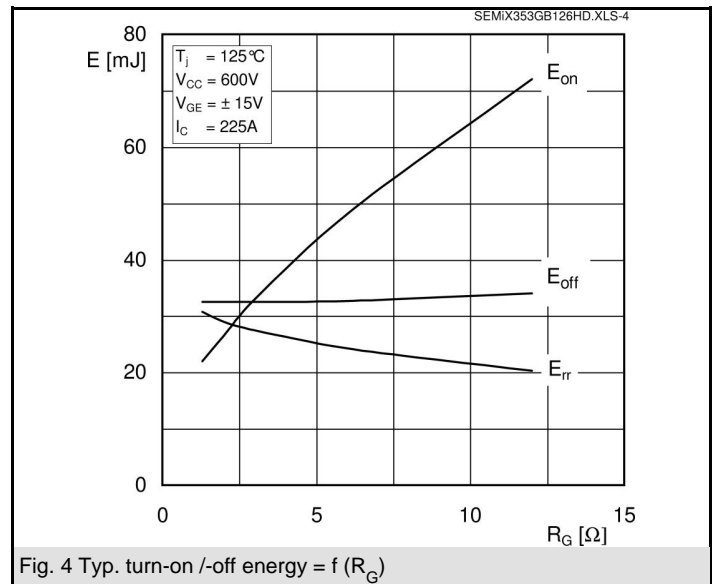
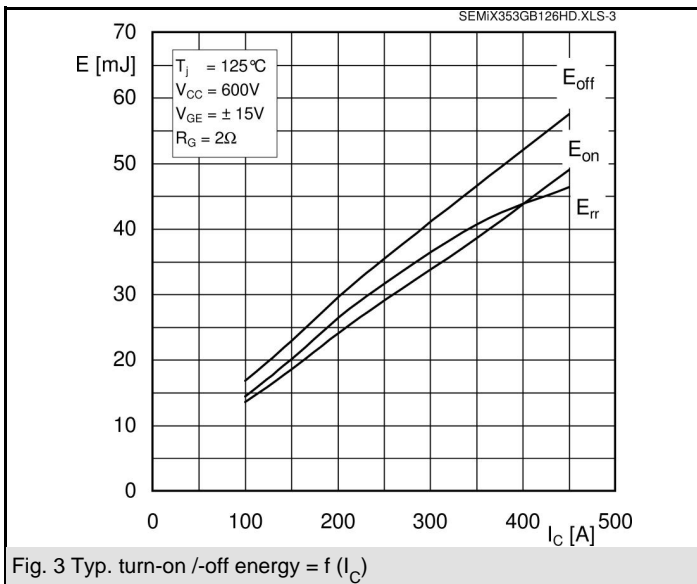
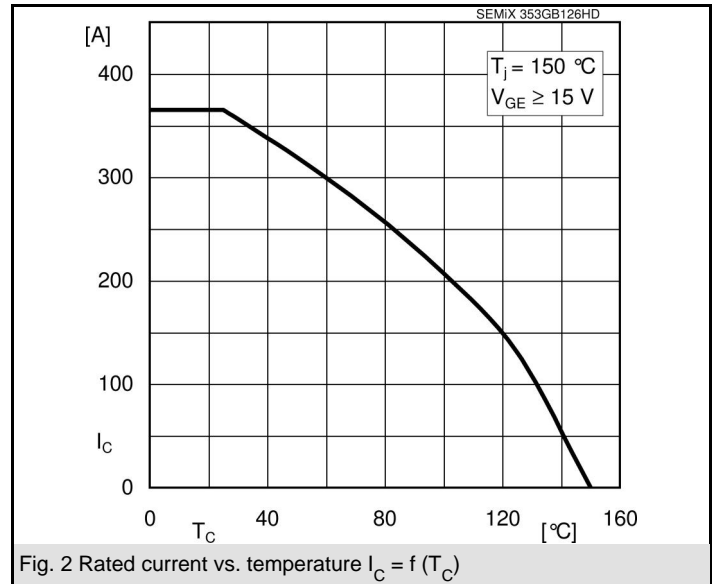
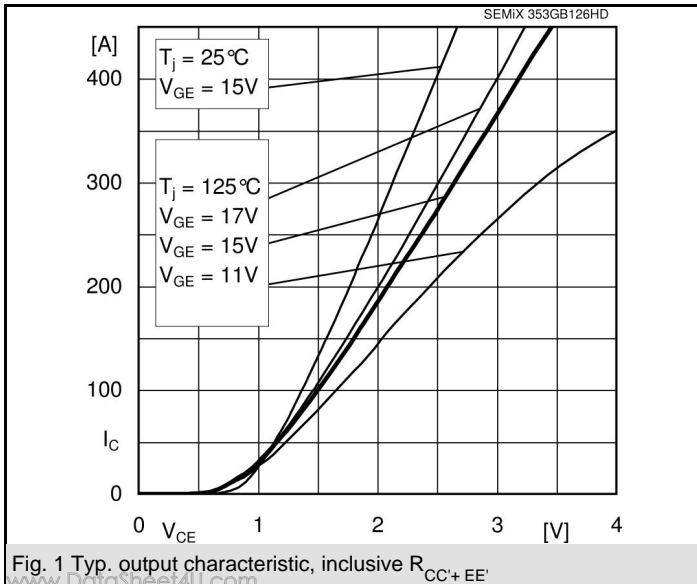
Characteristics		min.	typ.	max.	Units
<b>Inverse Diode</b>					
$V_F = V_{EC}$	$I_{Fnom} = 225 \text{ A}; V_{GE} = 0 \text{ V}$		1,6	1,8	V
	$T_j = 25^{\circ}\text{C}_{chiplev.}$				
	$T_j = 125^{\circ}\text{C}_{chiplev.}$		1,6	1,8	V
$V_{F0}$			1	1,1	V
	$T_j = 25^{\circ}\text{C}$				
	$T_j = 125^{\circ}\text{C}$		0,8	0,9	V
$r_F$			2,7	3,1	mΩ
	$T_j = 25^{\circ}\text{C}$				
	$T_j = 125^{\circ}\text{C}$		3,6	4	mΩ
$I_{RRM}$	$I_{Fnom} = 225 \text{ A}$		330		A
$Q_{rr}$	$di/dt = 5600 \text{ A}/\mu\text{s}$		69		μC
$E_{rr}$	$V_{GE} = -15 \text{ V}; V_{CC} = 600 \text{ V}$		29		mJ
$R_{th(j-c)D}$	per diode			0,17	K/W
<b>Module</b>					
$L_{CE}$			20		nH
$R_{CC'+EE'}$	res., terminal-chip	$T_{case} = 25^{\circ}\text{C}$	0,7		mΩ
		$T_{case} = 125^{\circ}\text{C}$	1		mΩ
$R_{th(c-s)}$	per module		0,04		K/W
$M_s$	to heat sink (M5)		3	5	Nm
$M_t$	to terminals (M6)		2,5	5	Nm
w				300	g
<b>Temperature sensor</b>					
$R_{100}$	$T_c = 100^{\circ}\text{C}$ ( $R_{25} = 5 \text{ k}\Omega$ )		0,493±5%		kΩ
$B_{100/125}$	$R(T) = R_{100} \exp[B_{100/125} (1/T - 1/T_{100})]$ ; $T[\text{K}]; B$		3550±2%		K

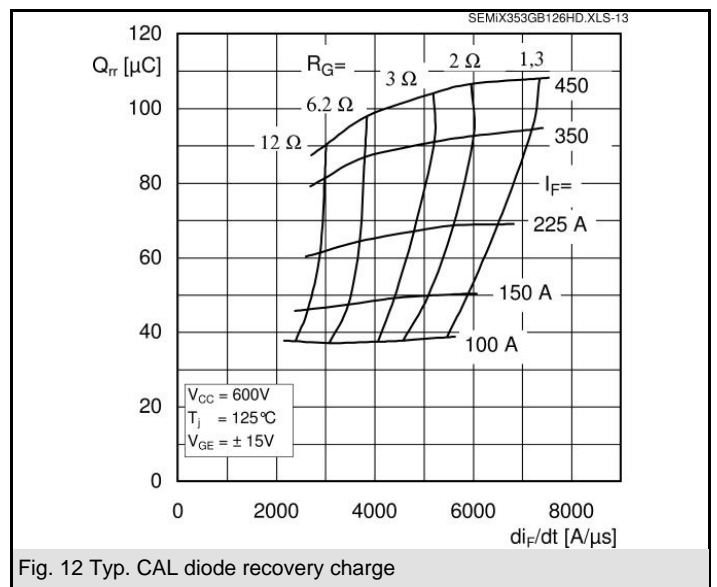
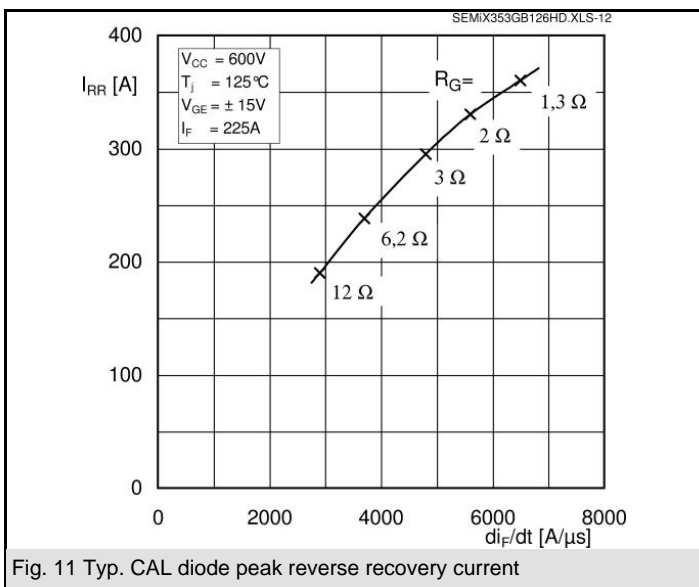
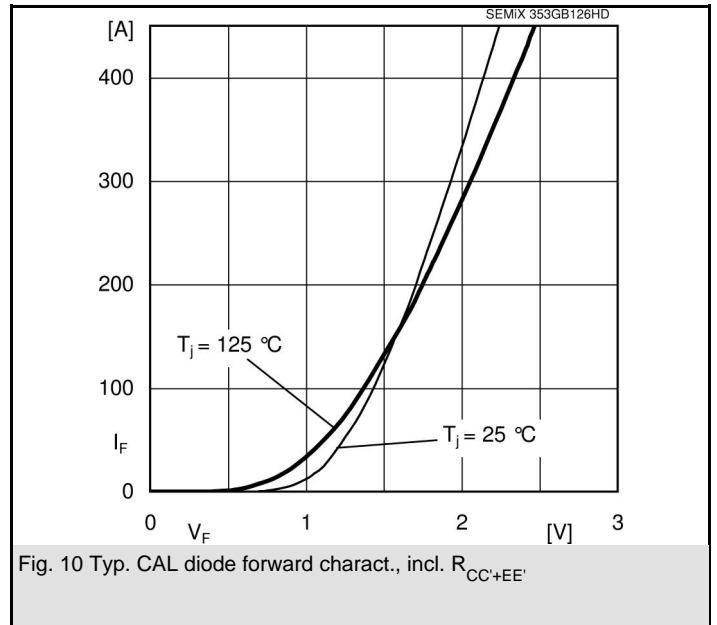
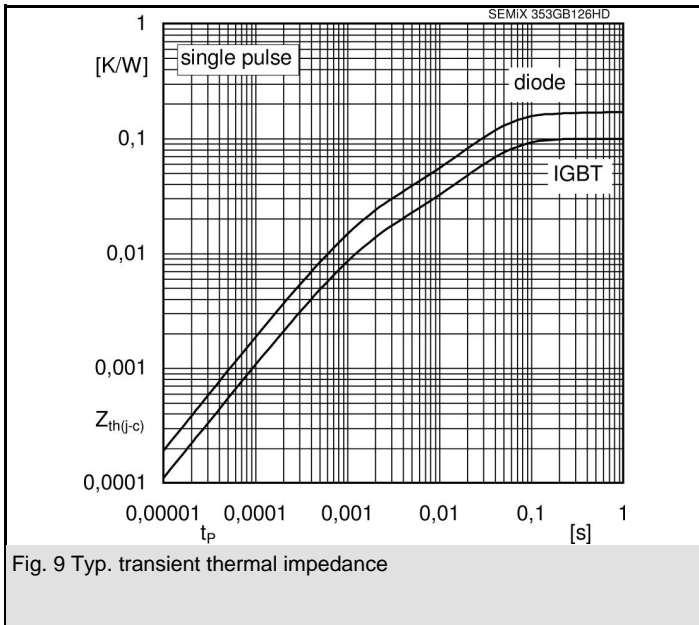
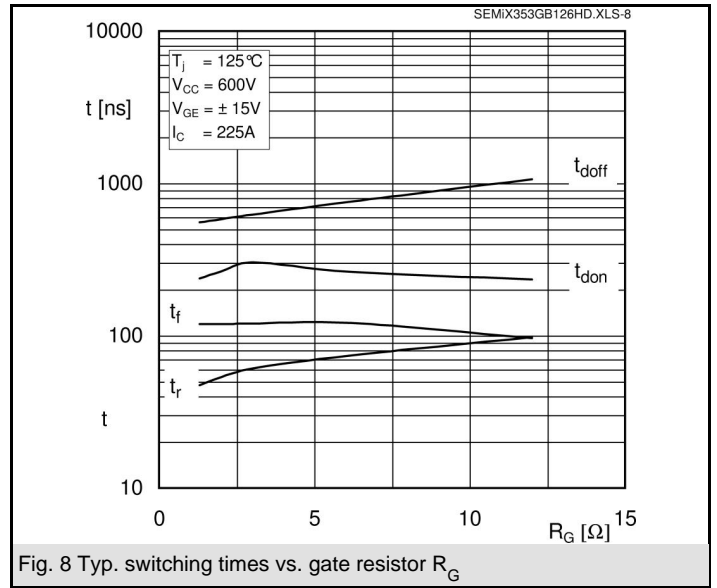
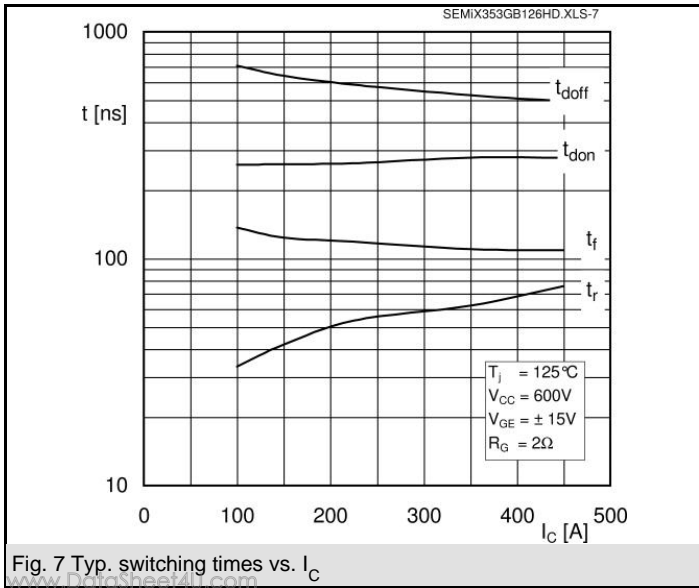
This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.



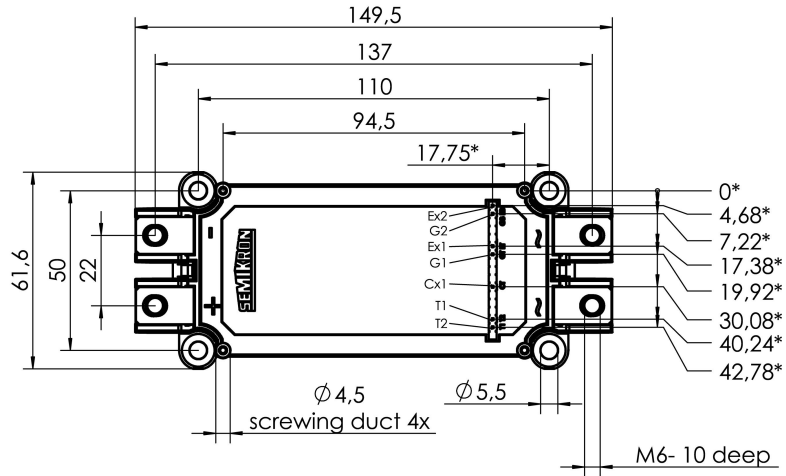
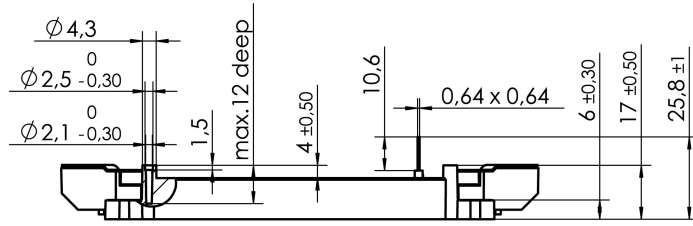
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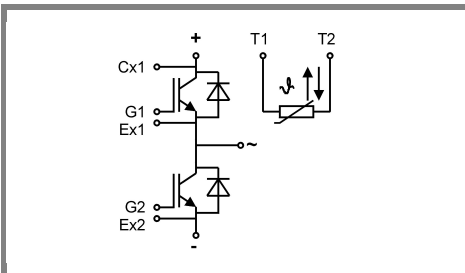
# SEMiX 353GB126HD

case: SEMiX 3



\* = all measures with  $\pm 0,5$

Case SEMiX 3



Pinout

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